

DESCRIPTION

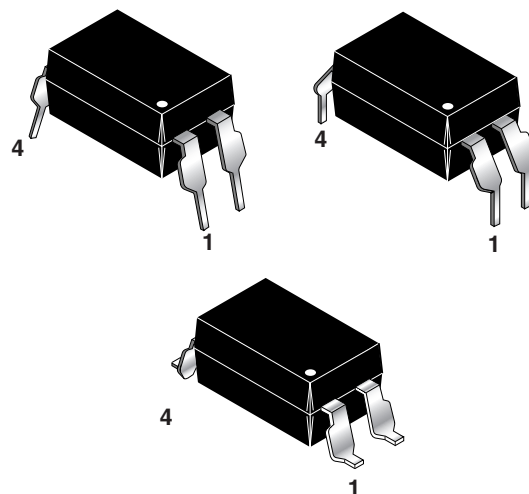
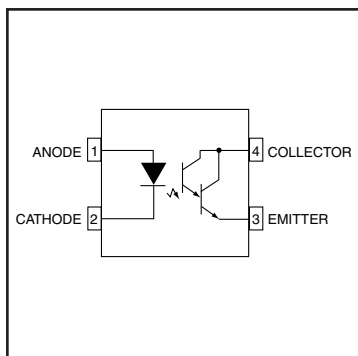
The H11B815 consists of a gallium arsenide infrared emitting diode driving a silicon Darlington phototransistor in a 4-pin dual in-line package.

FEATURES

- Compact 4-pin package
- Current Transfer Ratio: 600% minimum (at $I_F = 1 \text{ mA}$)
- High isolation voltage between input and output (5300 VRMS)
- UL recognized (File # E90700)

APPLICATIONS

- Power Supply Monitors
- Relay Contact Monitor
- Telephone/Telegraph Line Receiver
- Twisted Pair Line Receiver
- Digital Logic/Digital Logic



ABSOLUTE MAXIMUM RATINGS (No derating required up to 85°C)

Parameter	Symbol	Value	Units
TOTAL DEVICE			
Storage Temperature	T _{STG}	-55 to +150	°C
Operating Temperature	T _{OPR}	-55 to +100	°C
Lead Solder Temperature	T _{SOL}	260 for 10 sec	°C
Total Device Power Dissipation @ T _A = 25°C	P _D	250	mW
EMITTER			
DC/Average Forward Input Current	I _F	80	mA
Reverse Input Voltage	V _R	6	V
Forward Current - Peak (1μs pulse, 300pps)	I _{F(pk)}	1	A
LED Power Dissipation @ T _A = 25°C	P _D	140	mW
Derate above 25°C		1.33	mW/°C
DETECTOR			
Collector-Emitter Voltage	V _{CEO}	35	V
Emitter-Collector Voltage	V _{ECO}	6	V
Continuous Collector Current	I _C	200	mA
Detector Power Dissipation @ T _A = 25°C	P _D	200	mW
Derate above 25°C		2.0	mW/°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C Unless otherwise specified.)

INDIVIDUAL COMPONENT CHARACTERISTICS

Parameter	Test Conditions	Symbol	Min	Typ**	Max	Unit
EMITTER						
Input Forward Voltage	(I _F = 20 mA)	V _F		1.2	1.50	V
Reverse Leakage Current	(V _R = 6.0 V)	I _R		0.001	10	μA
DETECTOR						
Collector-Emitter Breakdown Voltage	(I _C = 1.0 mA, I _F = 0)	BV _{CEO}	35	60		V
Emitter-Collector Breakdown Voltage	(I _E = 100 μA, I _F = 0)	BV _{ECO}	6	8		V
Collector-Emitter Dark Current	(V _{CE} = 10 V, I _F = 0)	I _{CEO}		0.005	1	μA
Capacitance	(V _{CE} = 0 V, f = 1 MHz)	C _{CE}		8		pF

TRANSFER CHARACTERISTICS

DC Characteristic	Test Conditions	Symbol	Min	Typ**	Max	Units
Current Transfer Ratio, Collector-Emitter	(I _F = 1 mA, V _{CE} = 2 V)	CTR	600		7,500	%
Saturation Voltage	(I _F = 20 mA, I _C = 5 mA)	V _{CE(sat)}		0.8	1.0	V
Rise Time (non saturated)	(I _C = 10 mA, V _{CE} = 2 V, R _L = 100Ω)	t _r			300	μs
Fall Time (non saturated)	(I _C = 10 mA, V _{CE} = 2 V, R _L = 100Ω)	t _f			250	μs

ISOLATION CHARACTERISTICS

Characteristic	Test Conditions	Symbol	Min	Typ**	Max	Units
Input-Output Isolation Voltage	(I _{I-O} ≤ 1 μA, 1 min.)	V _{ISO}	5300			Vac(rms)
Isolation Resistance	(V _{I-O} = 500 VDC)	R _{ISO}	10 ¹¹			Ω
Isolation Capacitance	(V _{I-O} = ∅, f = 1 MHz)	C _{ISO}		0.5		pf

** All typicals at T_A = 25°C

TYPICAL PERFORMANCE CURVES

Fig. 1 Normalized Current Transfer Ratio vs. Forward Current

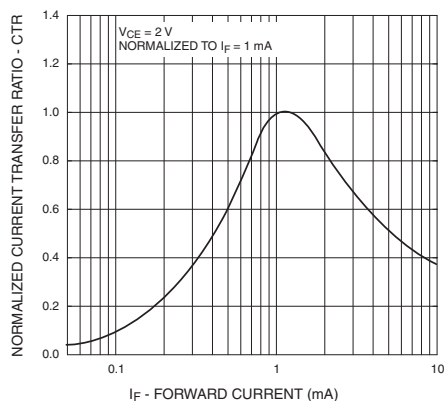


Fig. 2 Normalized Current Transfer Ratio vs. Ambient Temperature

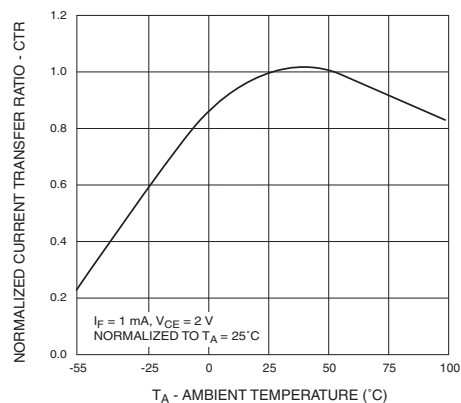


Fig. 3 Normalized Collector Current vs. Collector Emitter Voltage

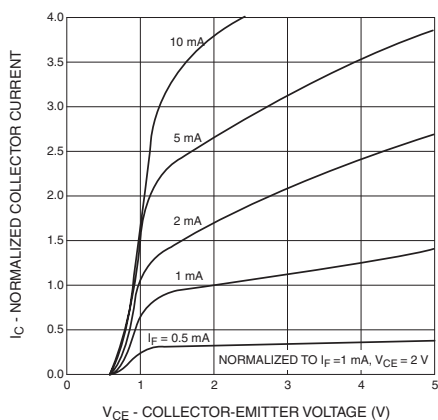


Fig. 4 Collector-Emitter Dark Current vs. Ambient Temperature

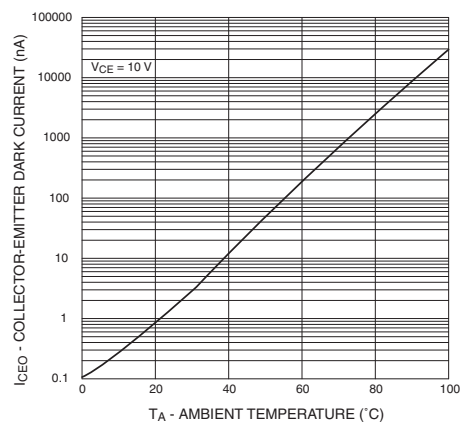
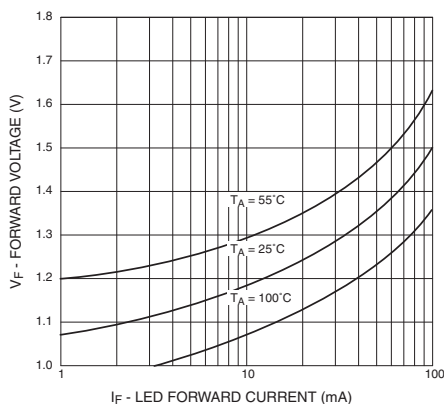
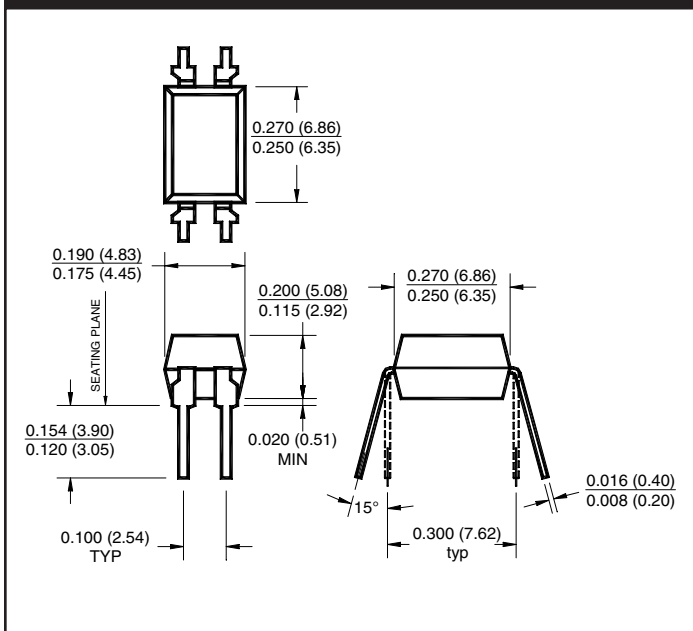


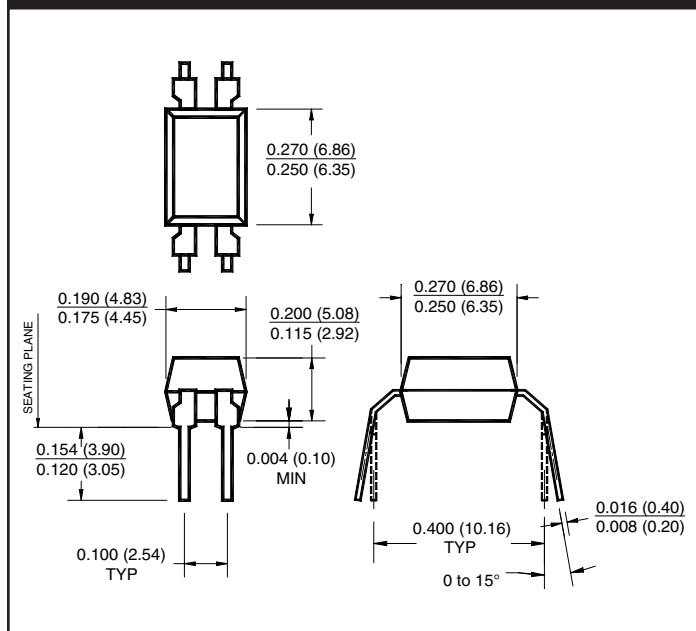
Fig. 5 LED Forward Voltage vs. Forward Current



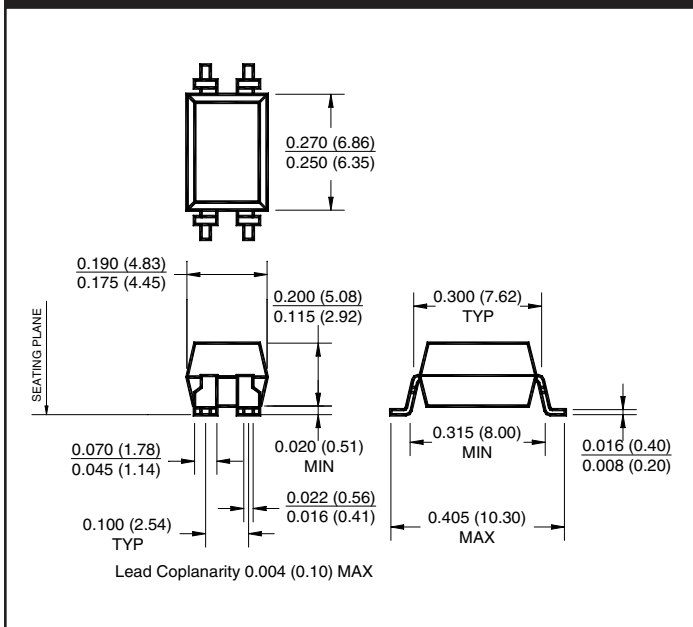
Package Dimensions (Through Hole)



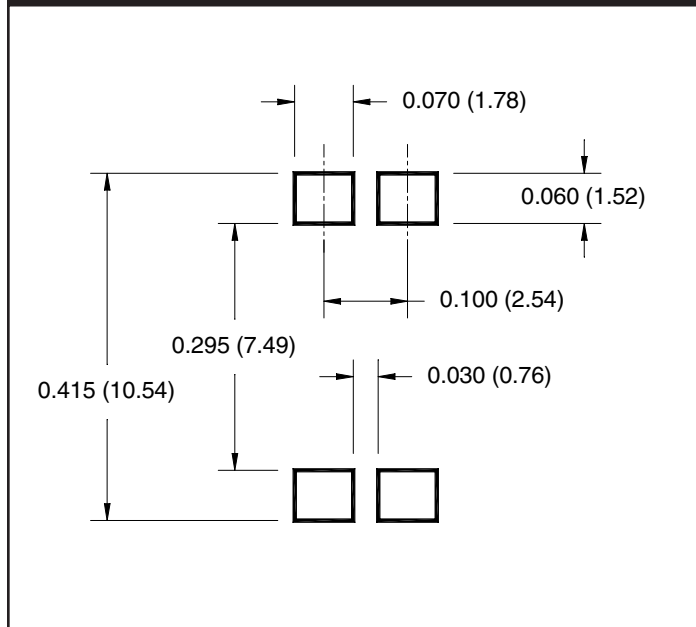
Package Dimensions (0.4"Lead Spacing)



Package Dimensions (0.4"Lead Spacing)



4 - Pin Dip



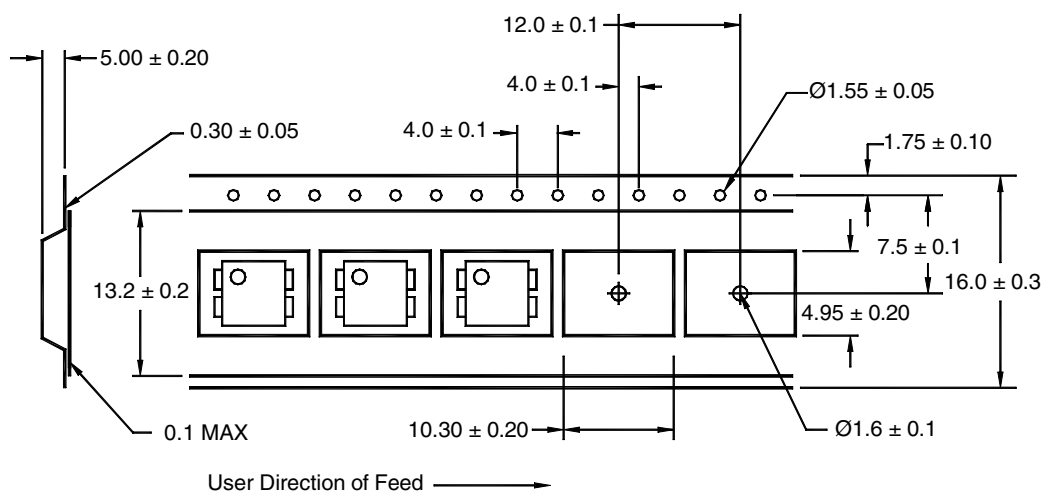
NOTE

All dimensions are in inches (millimeters)

ORDERING INFORMATION

Option	Order Entry Identifier	Description
S	.S	Surface Mount Lead Bend
SD	.SD	Surface Mount; Tape and reel
W	.W	0.4" Lead Spacing
300	.300	VDE 0884
300W	.300W	VDE 0884, 0.4" Lead Spacing
3S	.3S	VDE 0884, Surface Mount
3SD	.3SD	VDE 0884, Surface Mount, Tape & Reel

Carrier Tape Specifications ("D" Taping Orientation)



NOTE

All dimensions are millimeters

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